

# PMBTA44-Q

# 400 V, 0.3 A NPN high-voltage low VCEsat transistor 26 April 2022 Product data sheet

## 1. General description

NPN high-voltage low  $V_{\text{CEsat}}$  transistor in a SOT23 (TO-236AB) small Surface-Mounted Device (SMD) plastic package.

### 2. Features and benefits

- Low current (max. 300 mA)
- High voltage (max. 400 V)
- Qualified according to AEC-Q101 and recommended for use in automotive applications

### 3. Applications

- · LED driver for LED chain module
- · LCD backlighting
- · High Intensity Discharge (HID) front lighting
- Automotive motor management
- · Hook switch for wired telecom
- Switch Mode Power Supply (SMPS)

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	400	V
I <sub>C</sub>	collector current		-	-	300	mA
h <sub>FE</sub>	DC current gain	$V_{CE}$ = 10 V; $I_{C}$ = 10 mA; $T_{amb}$ = 25 °C	50	-	200	

# 5. Pinning information

**Table 2. Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	3	С
2	E	emitter		اً ا
3	С	collector		В — (
				    E
			1	sym021
			30123	



### 400 V, 0.3 A NPN high-voltage low VCEsat transistor

# 6. Ordering information

#### **Table 3. Ordering information**

Type number	Package						
	Name	Description	Version				
PMBTA44-Q		plastic, surface-mounted package; 3 terminals; 1.9 mm pitch; 2.9 mm x 1.3 mm x 1 mm body	SOT23				

### 7. Marking

#### Table 4. Marking codes

Type number	Marking code[1]
PMBTA44-Q	W3%

<sup>[1] % =</sup> placeholder for manufacturing site code

# 8. Limiting values

#### **Table 5. Limiting values**

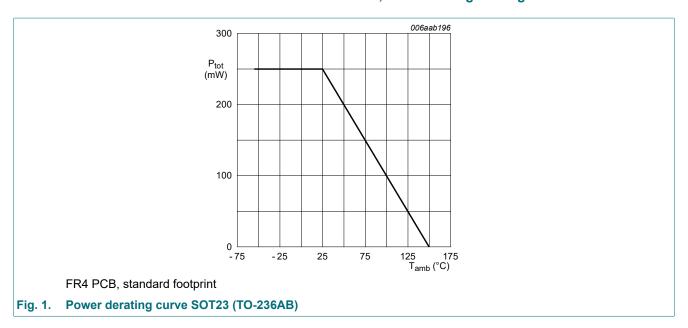
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{CBO}$	collector-base voltage	open emitter		-	500	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	400	V
$V_{EBO}$	emitter-base voltage	open collector		-	6	V
I <sub>C</sub>	collector current			-	300	mA
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	300	mA
I <sub>BM</sub>	peak base current			-	100	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	250	mW
T <sub>j</sub>	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

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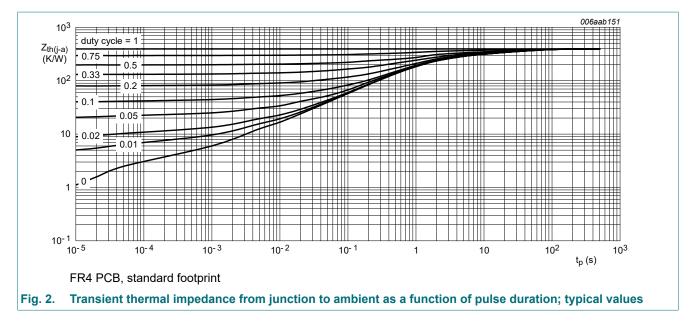


### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	[1]	-	-	500	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.



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### 10. Characteristics

**Table 7. Characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off	V <sub>CB</sub> = 320 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	100	nA
	current	V <sub>CB</sub> = 320 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	10	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	V <sub>EB</sub> = 4 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	100	nA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 10 V; I <sub>C</sub> = 10 mA; T <sub>amb</sub> = 25 °C	50	-	200	
		$V_{CE}$ = 10 V; $I_{C}$ = 50 mA; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	45	-	-	
		$V_{CE}$ = 10 V; $I_{C}$ = 100 mA; pulsed; $t_{p} \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	40	-	-	
V <sub>CEsat</sub>	collector-emitter	I <sub>C</sub> = 1 mA; I <sub>B</sub> = 0.1 mA; T <sub>amb</sub> = 25 °C	-	-	400	mV
	saturation voltage	$I_C$ = 10 mA; $I_B$ = 1 mA; $T_{amb}$ = 25 °C	-	-	500	mV
		$I_C$ = 50 mA; $I_B$ = 5 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-	750	mV
V <sub>BEsat</sub>	base-emitter saturation voltage	$I_C$ = 10 mA; $I_B$ = 1 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-	850	mV
f <sub>T</sub>	transition frequency	$V_{CE}$ = 10 V; $I_{C}$ = 10 mA; f = 100 MHz; $T_{amb}$ = 25 °C	20	-	-	MHz
C <sub>c</sub>	collector capacitance	$V_{CB} = 20 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A}; f = 1 \text{ MHz}; $ $T_{amb} = 25  ^{\circ}\text{C}$	-	-	7	pF
C <sub>e</sub>	emitter capacitance	$V_{EB} = 0.5 \text{ V}; I_{C} = 0 \text{ A}; i_{c} = 0 \text{ A};$ $f = 1 \text{ MHz}; T_{amb} = 25 ^{\circ}\text{C}$	-	-	180	pF

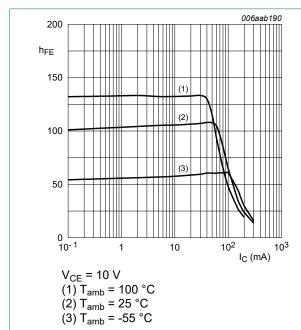


Fig. 3. DC current gain as a function of collector current; typical values

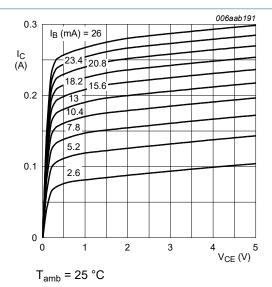
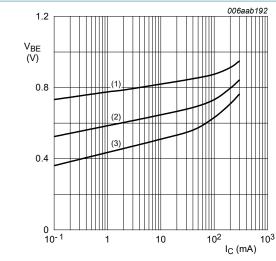


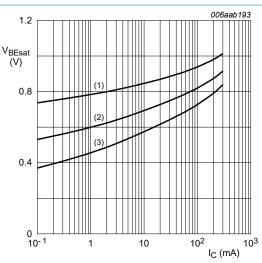
Fig. 4. Collector current as a function of collectoremitter voltage; typical values

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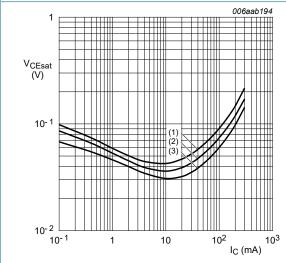
V<sub>CE</sub> = 10 V (1) T<sub>amb</sub> = -55 °C (2) T<sub>amb</sub> = 25 °C (3) T<sub>amb</sub> = 100 °C

Fig. 5. Base-emitter voltage as a function of collector current; typical values



I<sub>C</sub>/I<sub>B</sub> = 5 (1) T<sub>amb</sub> = -55 °C (2) T<sub>amb</sub> = 25 °C (3) T<sub>amb</sub> = 100 °C

Fig. 6. Base-emitter saturation voltage as a function of collector current; typical values



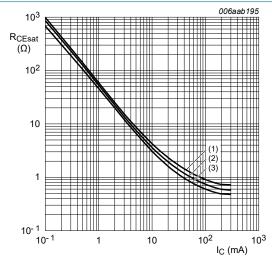
 $I_{\rm C}/I_{\rm B}=5$ 

(1) T<sub>amb</sub> = 100 °C

(2)  $T_{amb} = 25 \, ^{\circ}C$ 

(3)  $T_{amb} = -55 \, ^{\circ}C$ 

Fig. 7. Collector-emitter saturation voltage as a function of collector current; typical values



 $I_C/I_B = 5$ 

(1) T<sub>amb</sub> = 100 °C

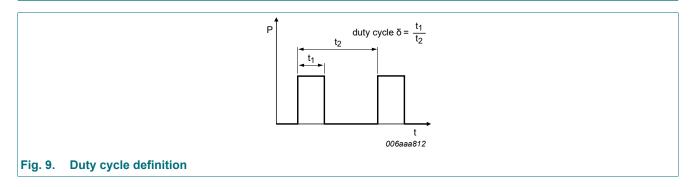
(2)  $T_{amb} = 25 \, ^{\circ}C$ 

(3)  $T_{amb} = -55 \, ^{\circ}C$ 

Fig. 8. Collector-emitter saturation resistance as a function of collector current; typical values

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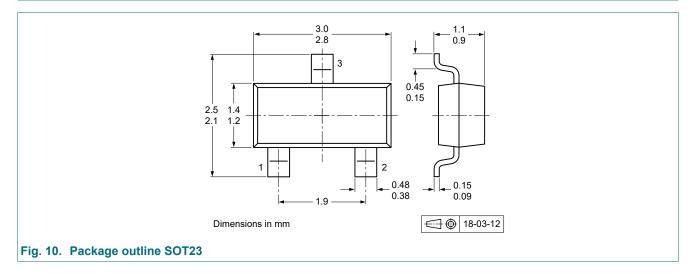
### 11. Test information



### **Quality information**

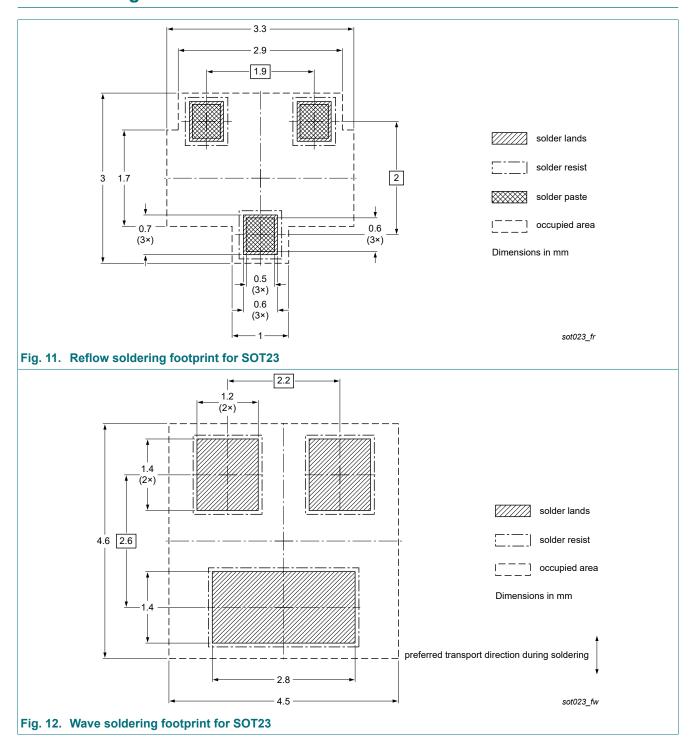
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

## 12. Package outline



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# 13. Soldering



400 V, 0.3 A NPN high-voltage low VCEsat transistor

# 14. Revision history

#### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMBTA44-Q v.1	20220426	Product data sheet	-	-

### 15. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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